

# Asian IBIS Summit (Tokyo)

## Board Design for Low Loss

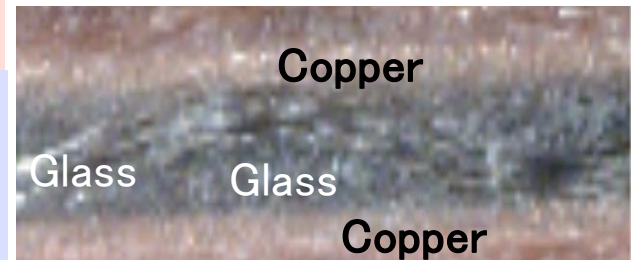
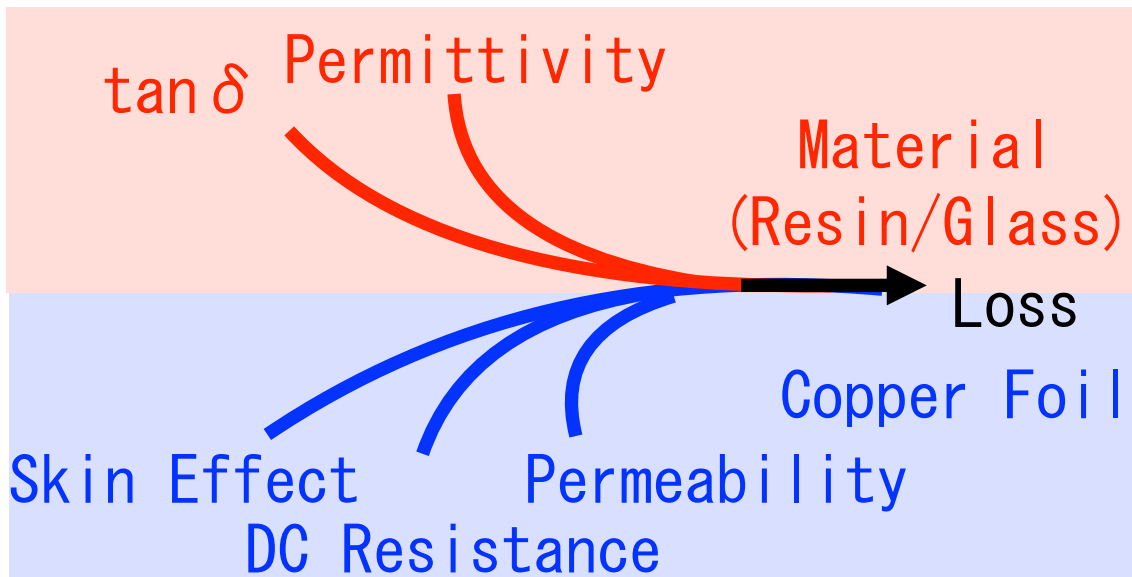
November 13, 2020

KEI Systems

Shinichi Maeda

# What is the loss

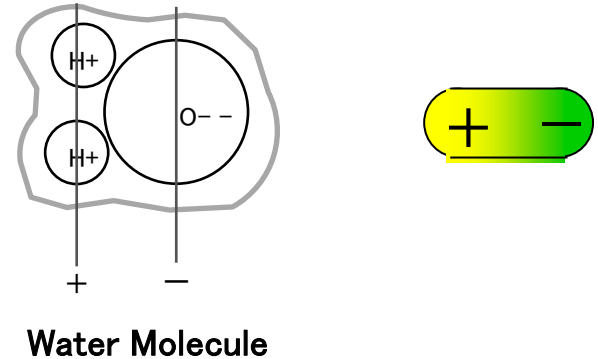
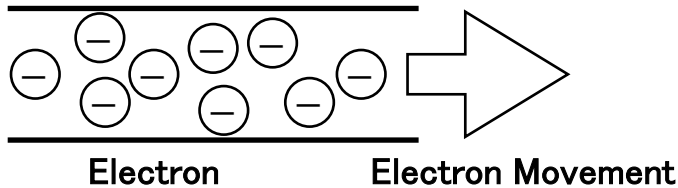
# Dielectric Loss & Resistance Loss



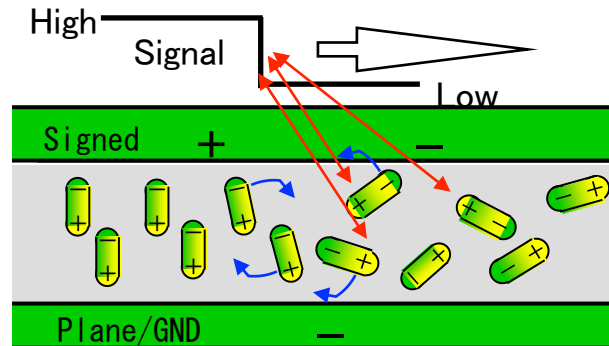
- Loss: Frequency and Etch Length
  - Dielectric Loss
    - Permittivity (  $\epsilon$  ) & Loss tangent (  $\tan \delta$  )
      - $D = K \cdot f \cdot \tan \delta \cdot \sqrt{\epsilon}$
  - Resistance Loss
    - Skin Effect (Skin Depth:  $d$ )
      - $d = \sqrt{\rho / \pi f \mu}$

# Dielectric Loss

- Conductor : Free Electron
- Dielectric : Electric Dipole



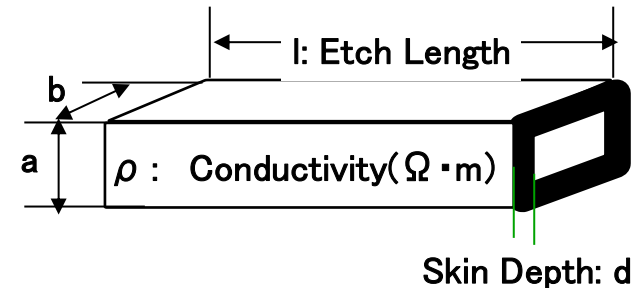
- When the potential between two layers change, the electric dipole spin by electric field changing
  - Permittivity : Energy loss by repulsive force between signal and dipole
  - tangent loss : Energy loss by spin dipole



# Resistance Loss

- Conductor (Copper) has small resistance

- Resistance :  $R = l \times \rho / S$   
(S: Cross-section area (a x b))



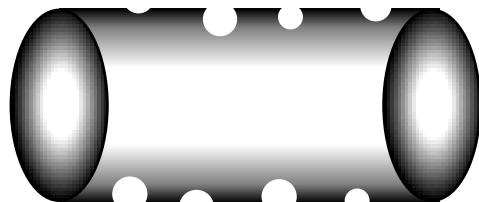
- Skin Effect

- When the current changes quickly, magnetic field is generated inside of conductor. This magnetic field generate current inside the conductor. Density of signal current becomes high of skincare, low of inside.

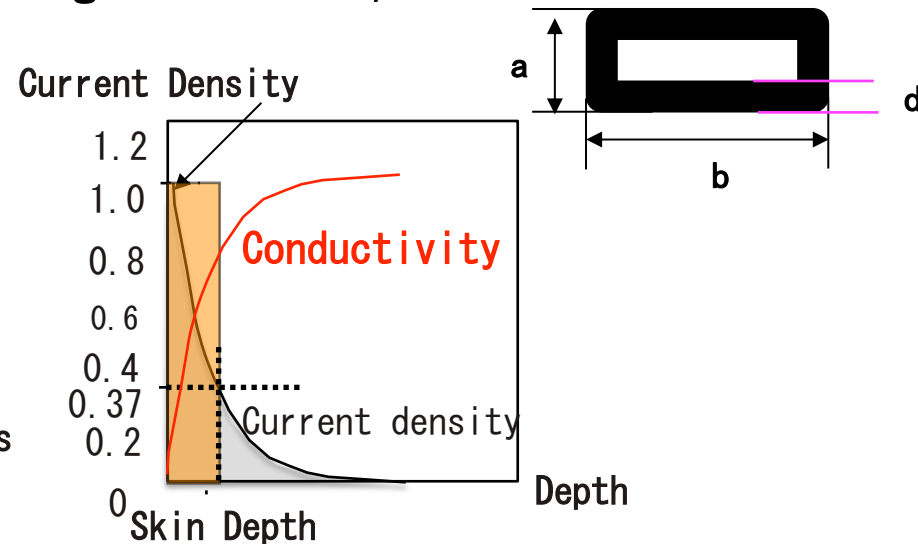
- Skin Depth :  $d = \sqrt{\rho / \pi f \mu}$

- Effective cross-section area:  $S1$

$$S1 = a \times b - (a-2d) \times (b-2d)$$



Surface Roughness



# Loss Simulation

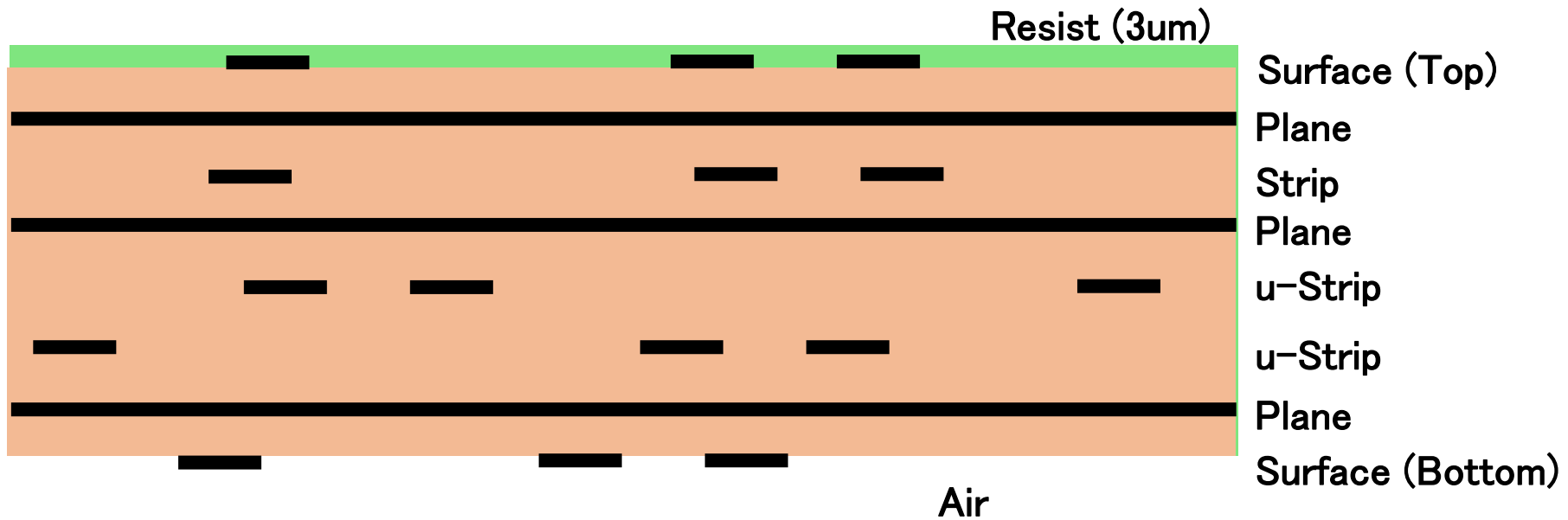
# Material

- Simulate three cases
  - General Use FR-4
  - Low Loss for High Frequency PCB
  - Super Low Loss for over 12GHz
- Resist Ink
  - Low Loss Ink (Most Resists are more lossy)
- Copper surface roughness is average of 4-sides

	FR-4	Low Loss	Super Low Loss	Resist Ink (Low Loss)
Dk(1GHz)	4.8	3.8	3.4	3.0
Dk(10GHz)		3.8	3.4	
Df(1GHz)	0.015	0.005	0.002	0.01
Df(10GHz)		0.007	0.004	
Cu Surface	3um	1um	1um	-

# Stack-up

- The Thickness of each layer is different to keep same single etch width (100  $\mu\text{m}$ ) and same impedance (50 ohm) of each condition.
- Etch Length = 30 cm (12")





# Simulation Case

- Single Line
  - Line width: 100 um, Impedance: 50 ohm
- Diff. Line
  - Line Width: 100 um, Single Line Impedance: 50 ohm
  - Diff. Line Space: 250um/100um/75um
  - Structure: u-Strip (Surface)/u-Strip (Inner)/Strip

	FR-4	Low Loss	Super Low Loss
Single	50	50	50
100/250	94~100	96~100	98~100
100/100	76~86	81~87	83~88
100/75	69~80	74~81	77~82

- High-Speed Serial Signal

	PCIe 3	PCIe 4	28Gbis	PCIe 5	PCIe 6	56 Gbps	112 Gbps
Signal Speed	4 GHz	8 GHz	14 GHz	16 GHz	16 GHz	14 GHz	28 GHz
	NRZ	NRZ	NRZ	NRZ	PAM4	PAM4	PAM4

# Simulation Results

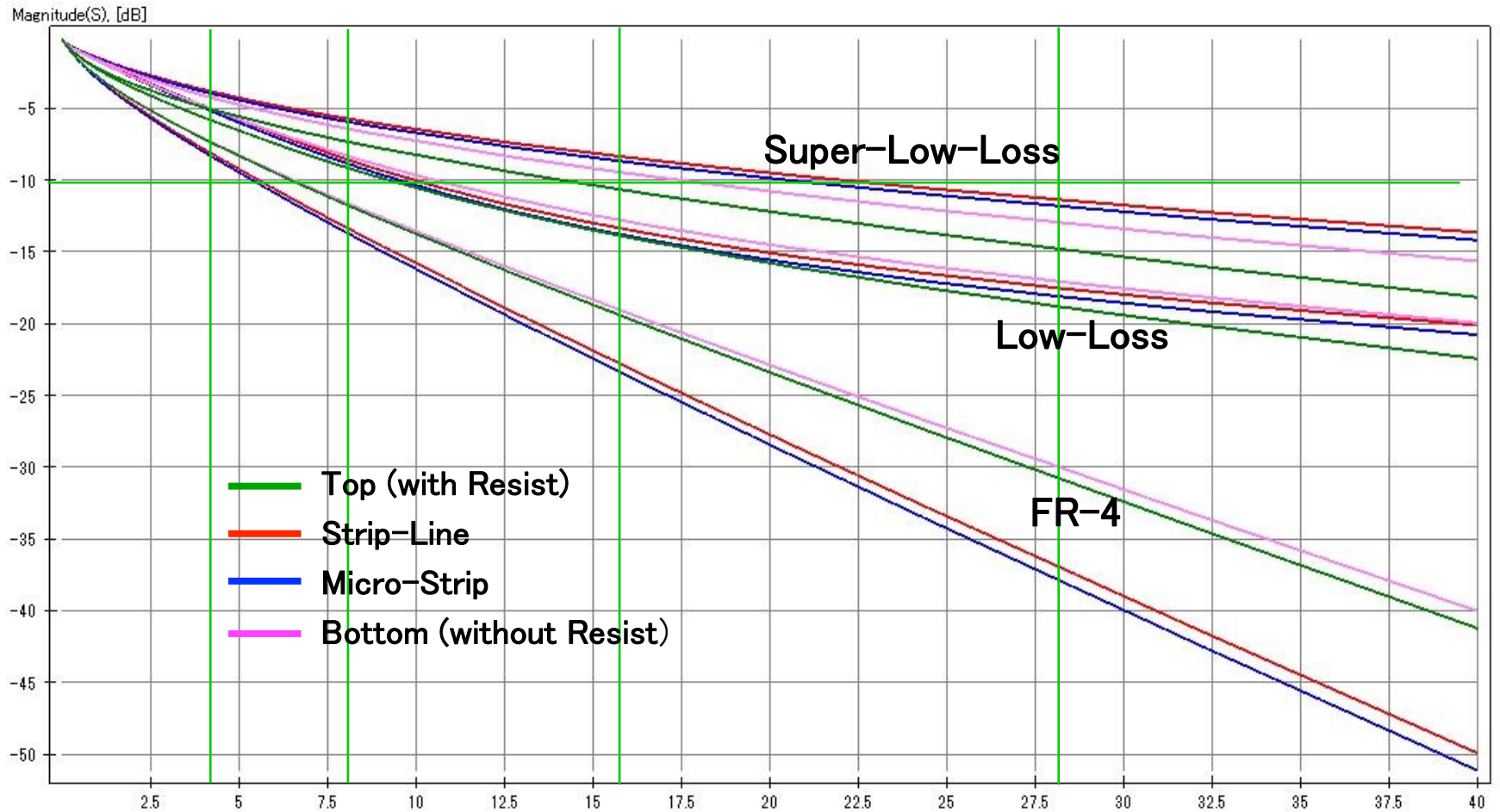


# Single Line



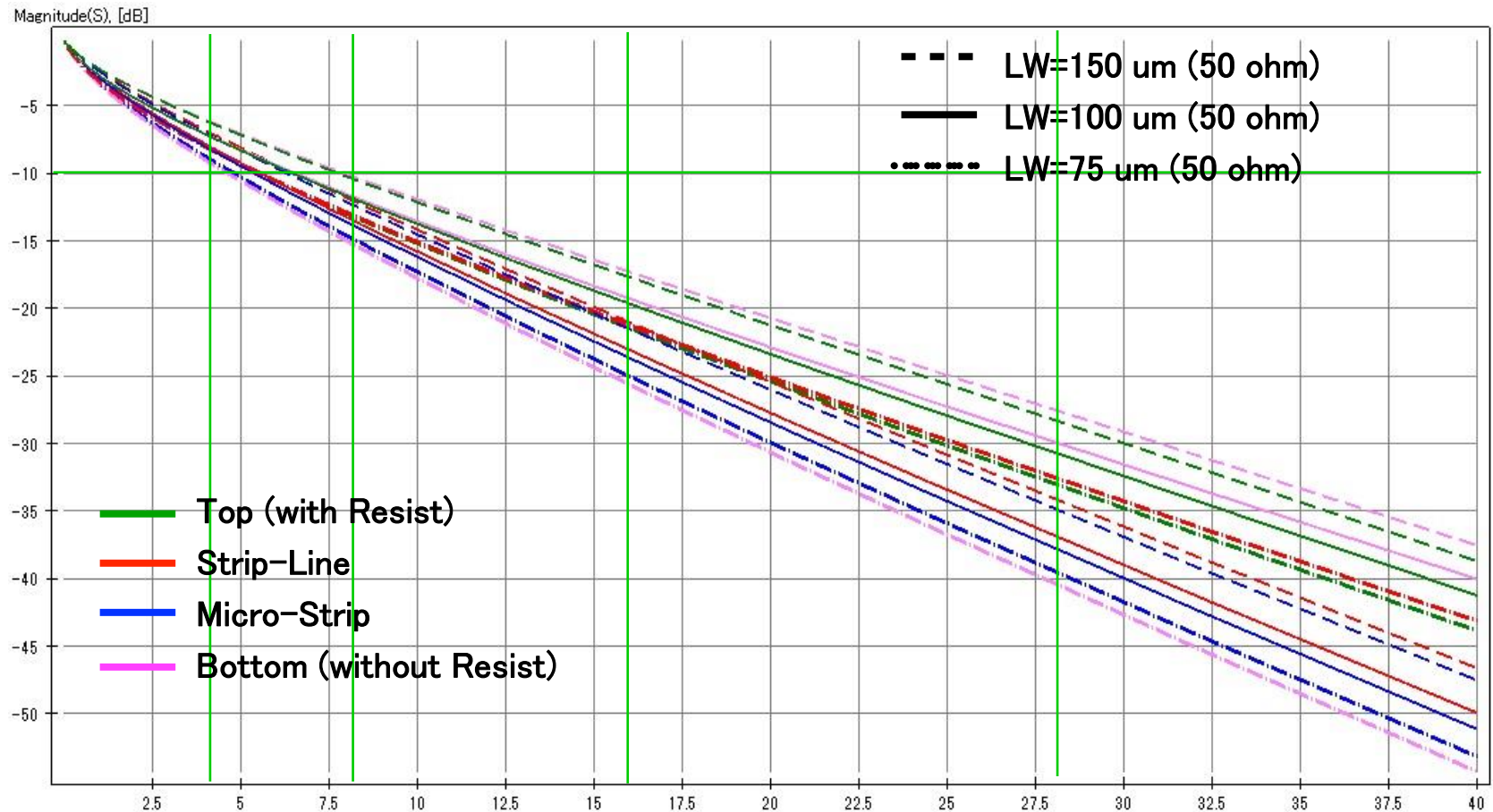
# Single 50 ohm

- Three Materials



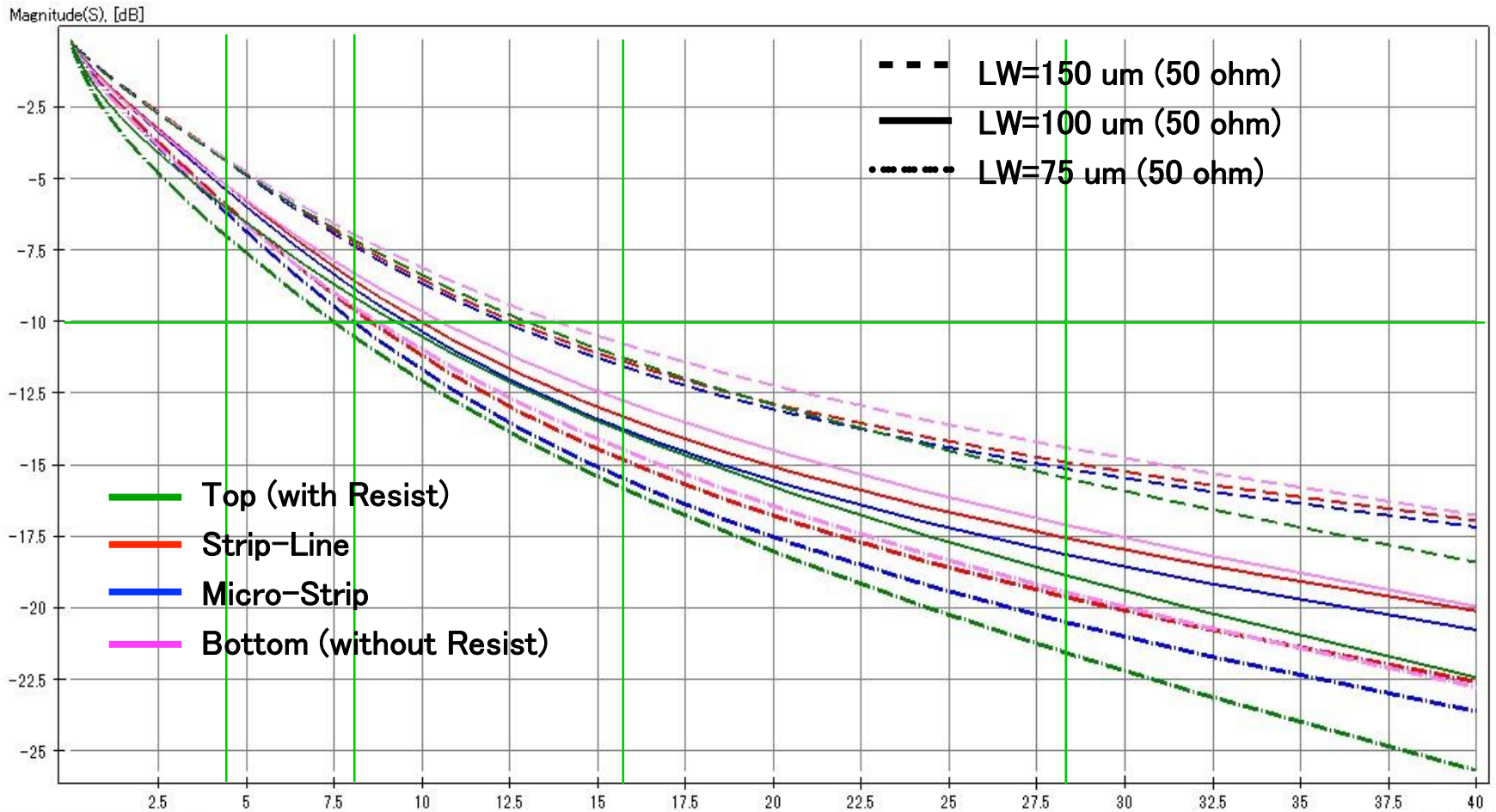
# FR-4 Material (Single 50 ohm)

- Different Line Width



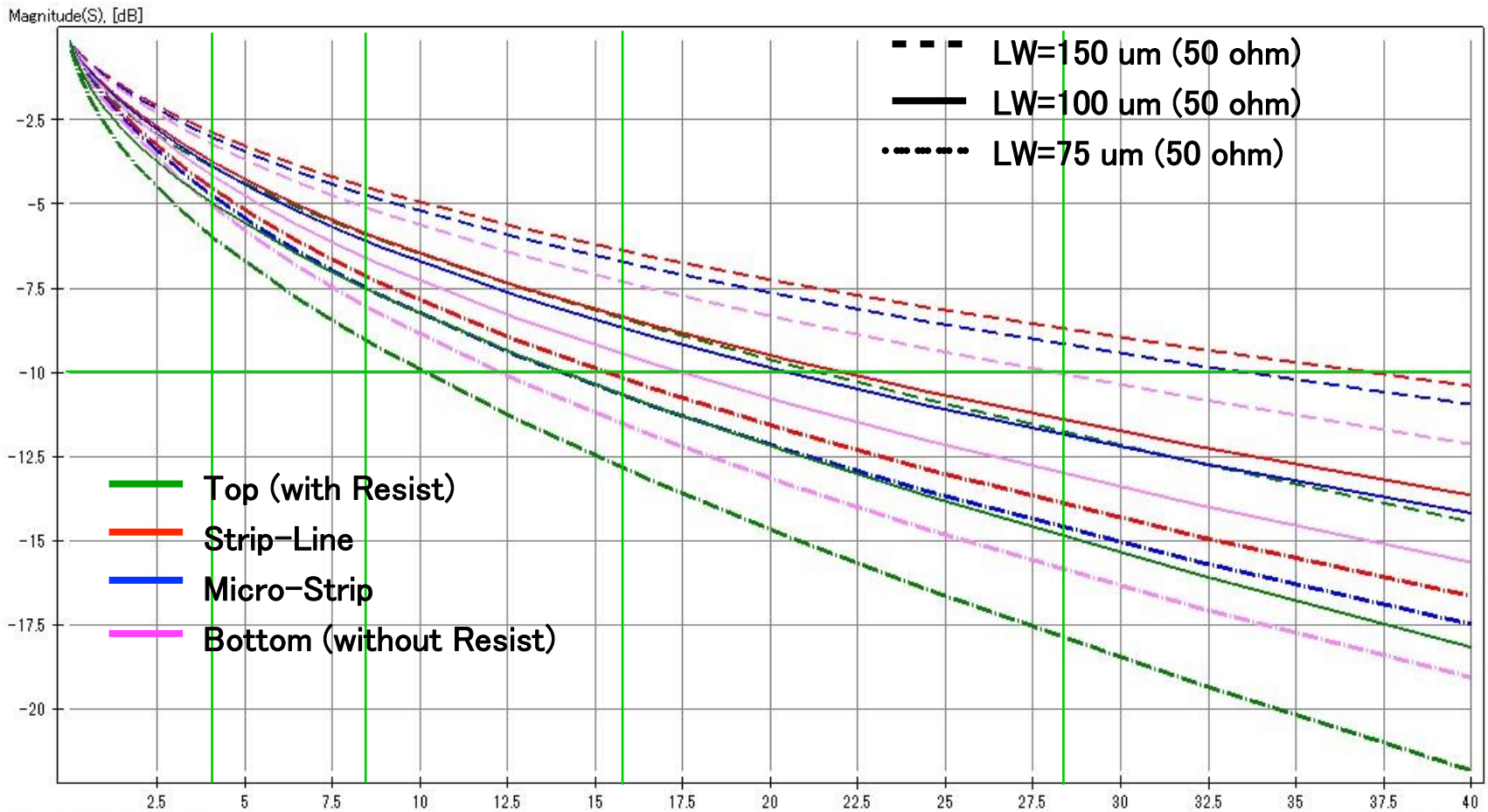
# Low-Loss Material (Single 50 ohm)

- Different Line Width



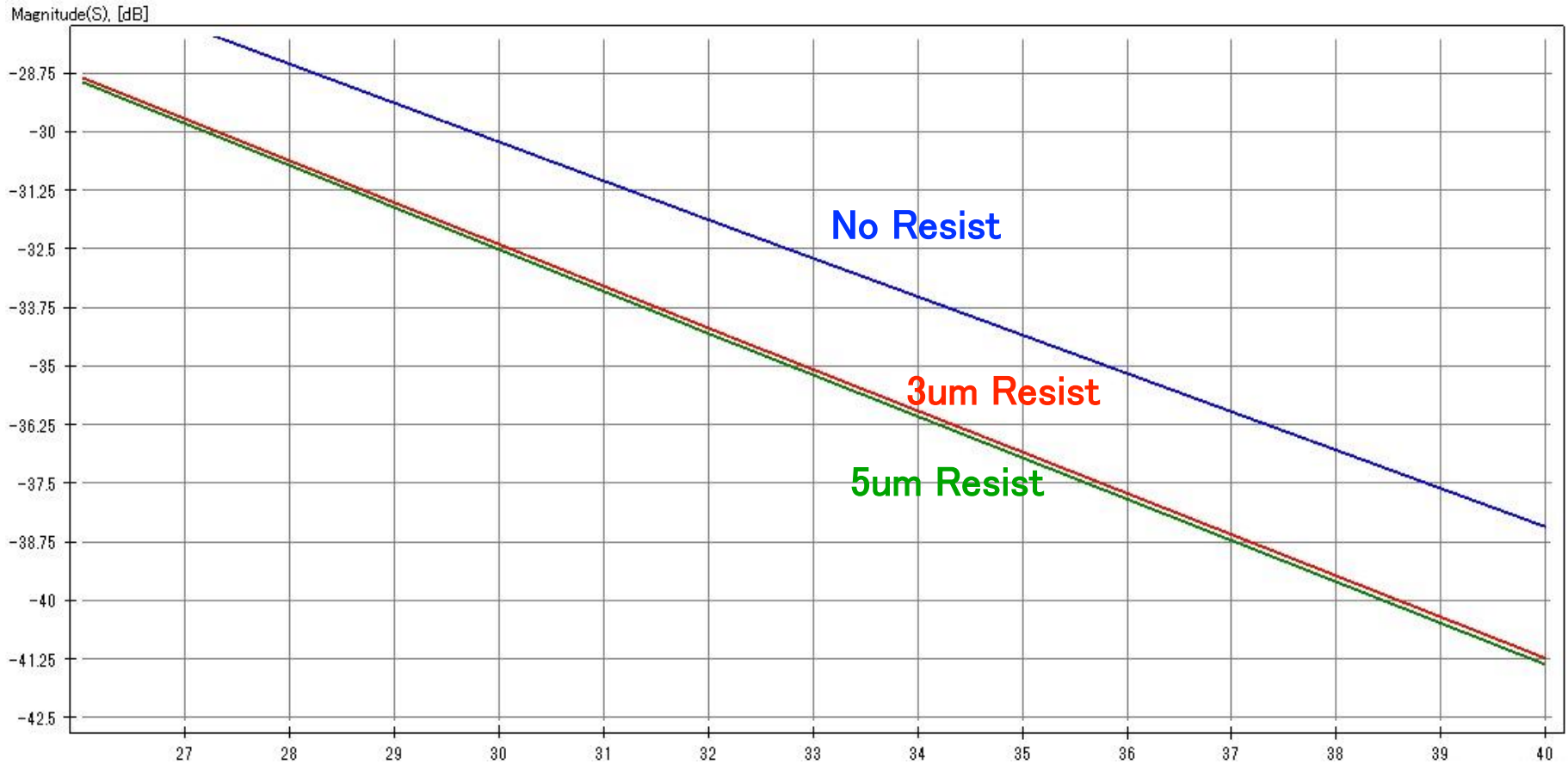
# Super-Low-Loss Material (Single 50 ohm)

- Different Line Width



# Effect of Resist ink

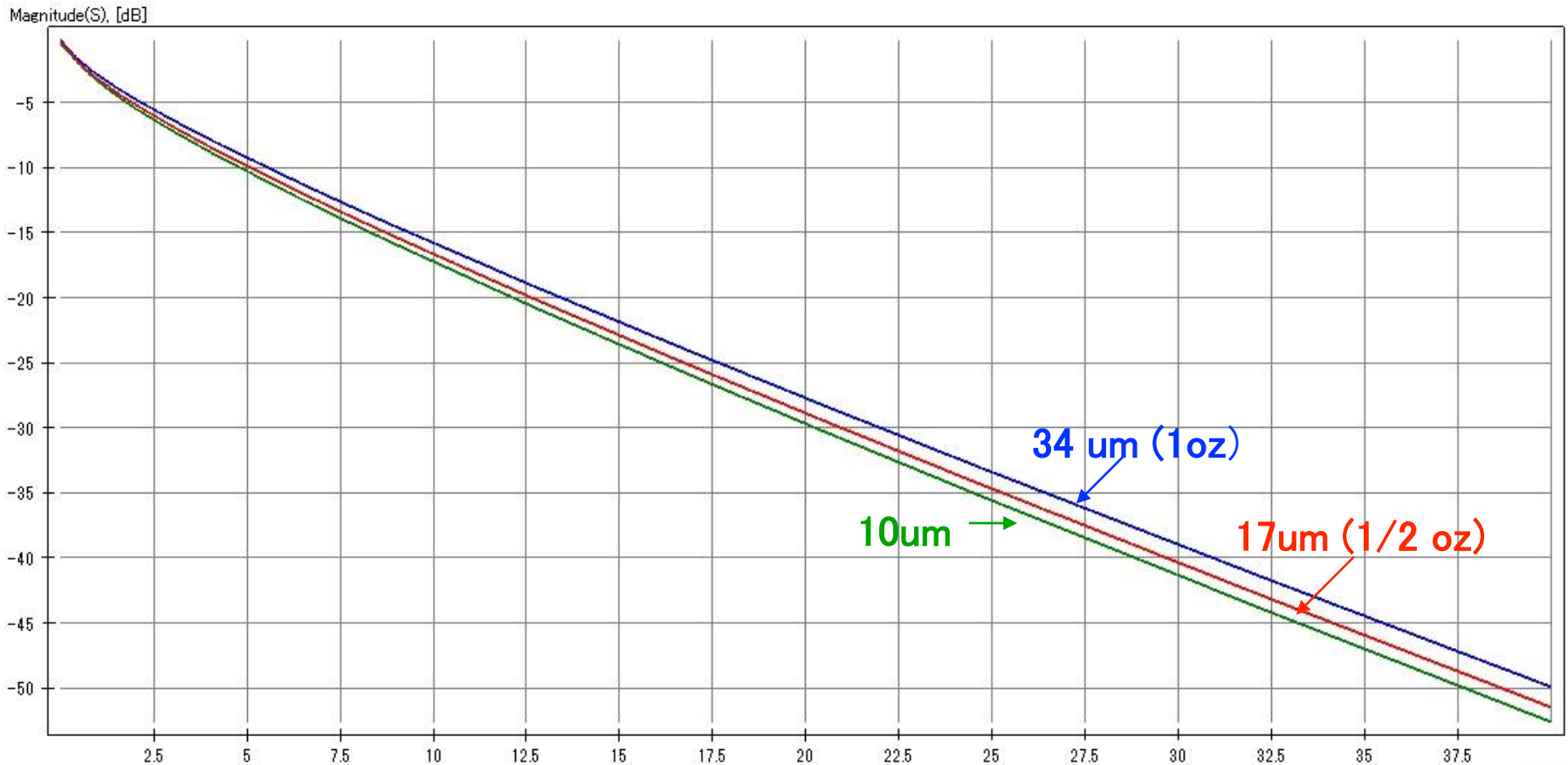
- FR-4 Top
- LW = 100  $\mu\text{m}$





# Effect of Copper Thickness

- FR-4 Strip Line
- LW = 100  $\mu\text{m}$

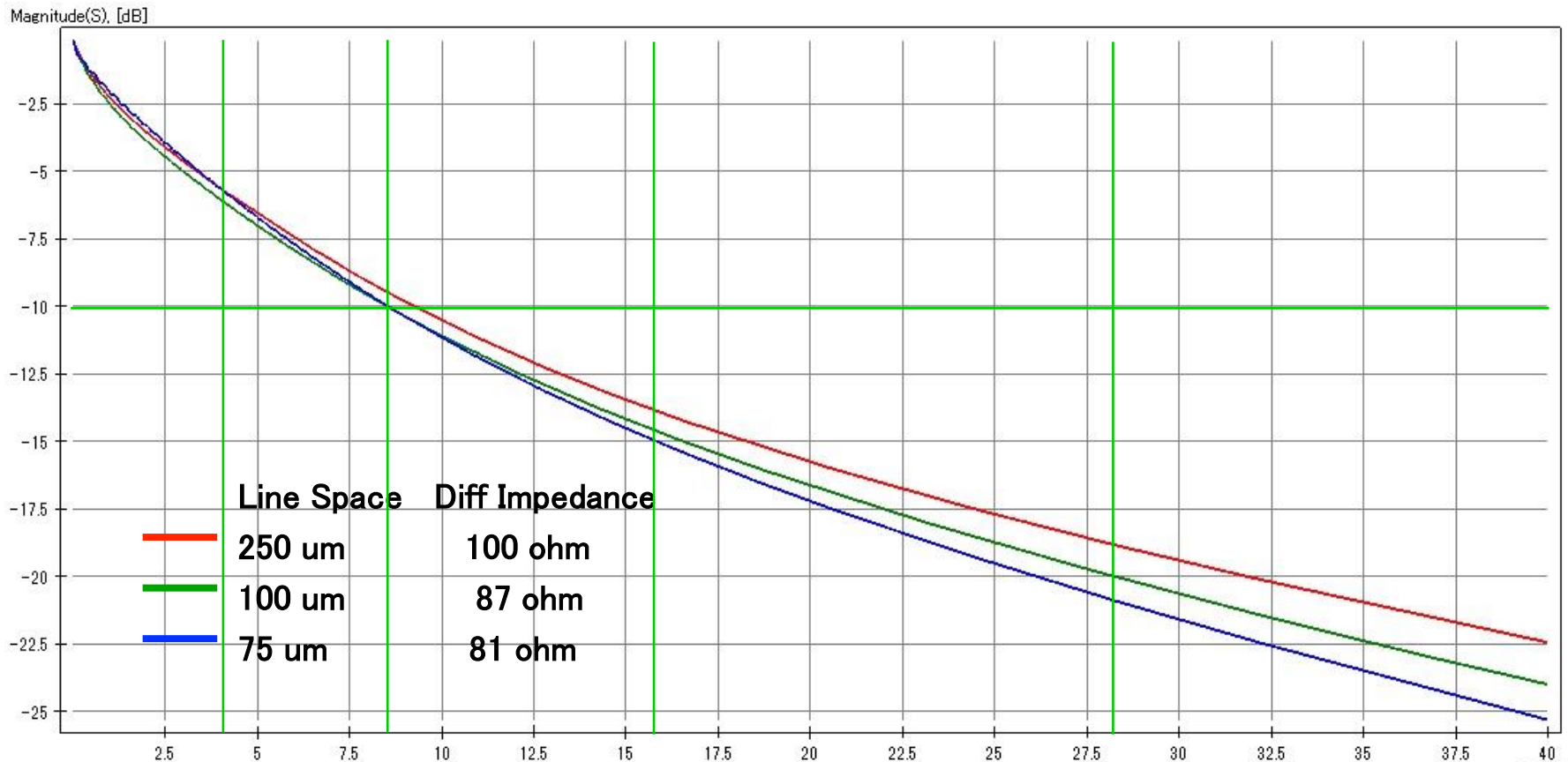


# Differential Line



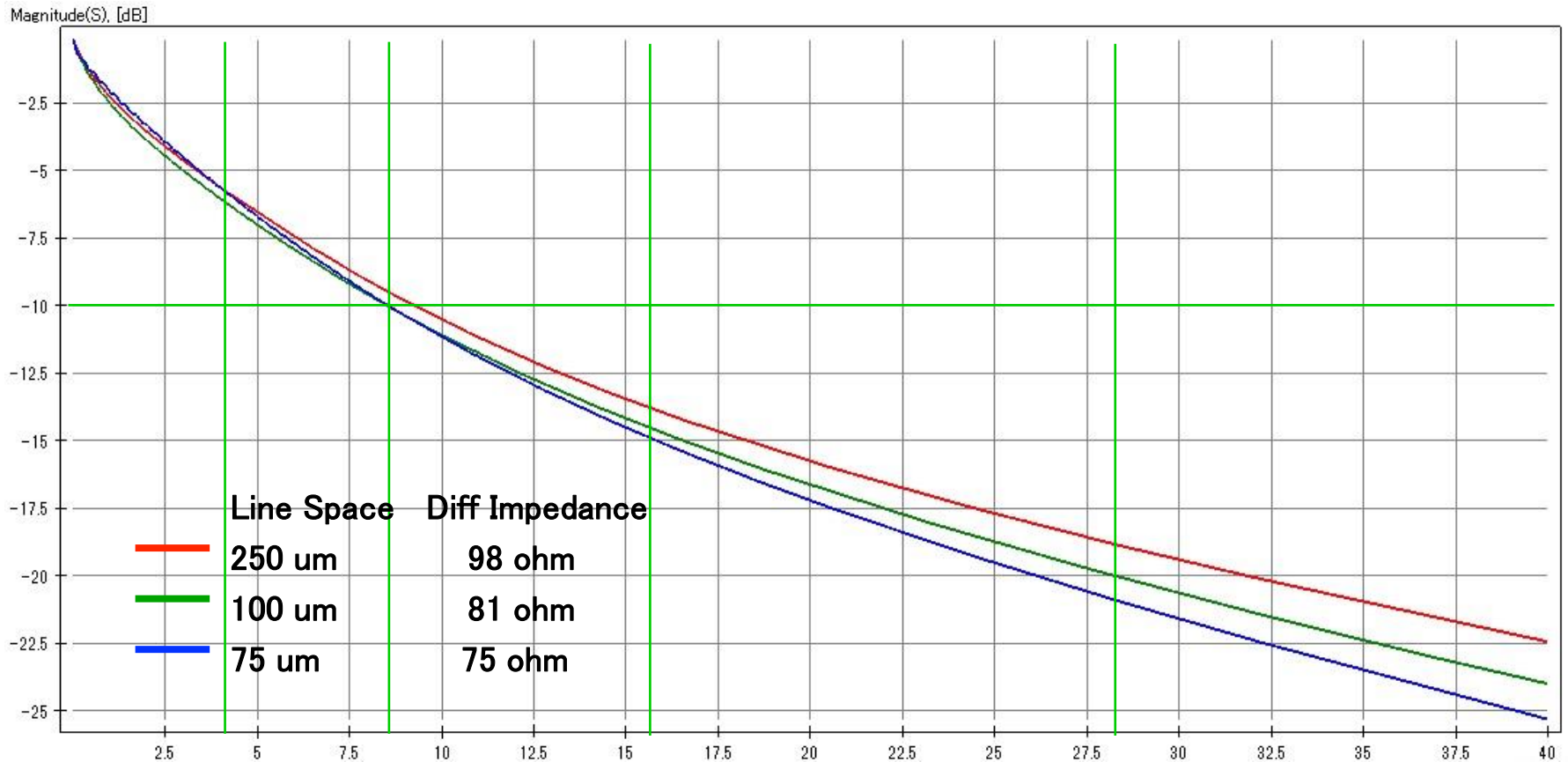
# Differential Line Space

- Low Loss Material, Top Layer
  - Line Width: 100 $\mu$ m (Single Line Impedance = 50 ohm)



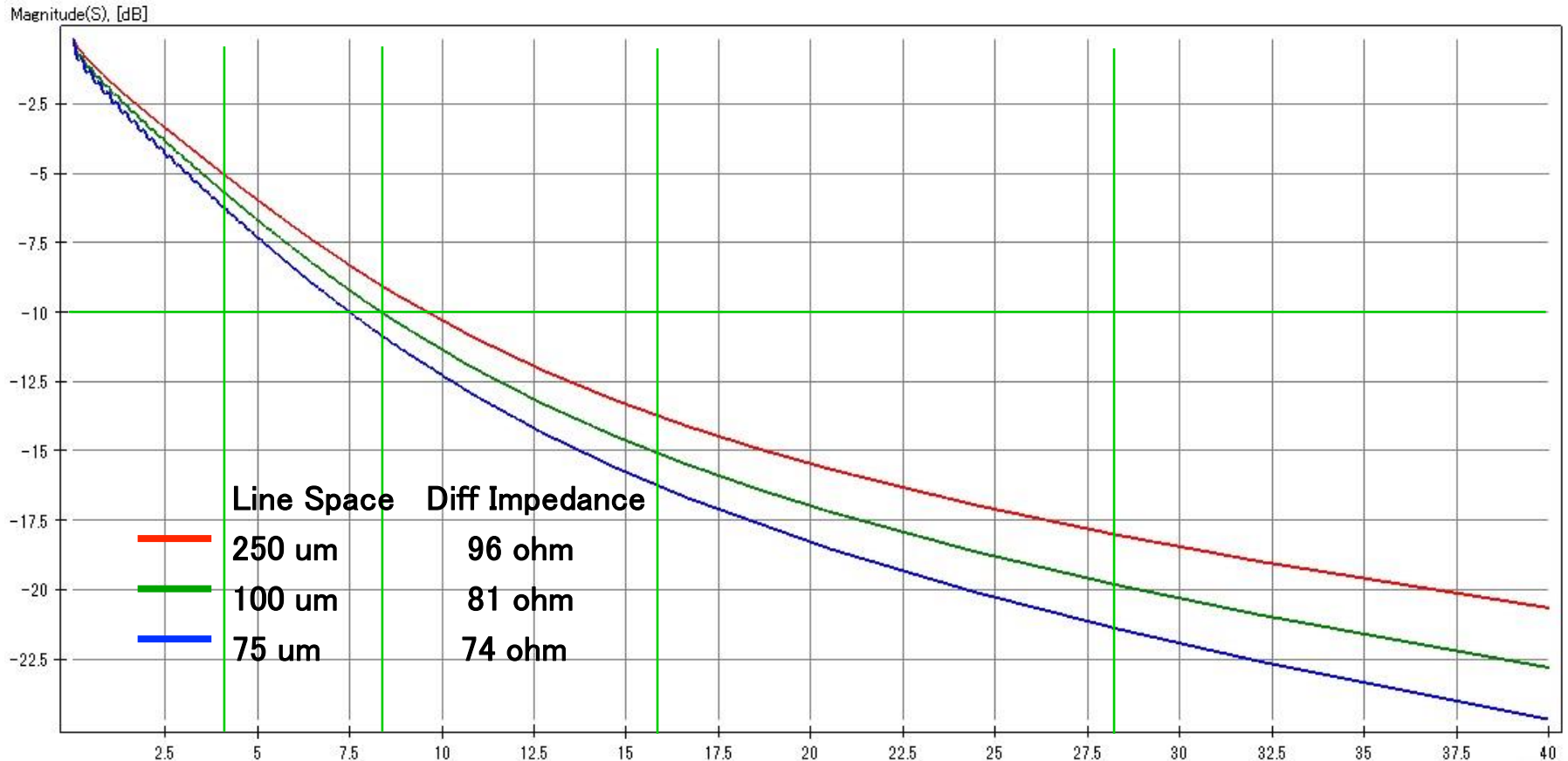
# Differential Line Space

- Low Loss Material, Strip-line
  - Line Width: 100 $\mu$ m (Single Line Impedance = 50 ohm)



# Differential Line Space

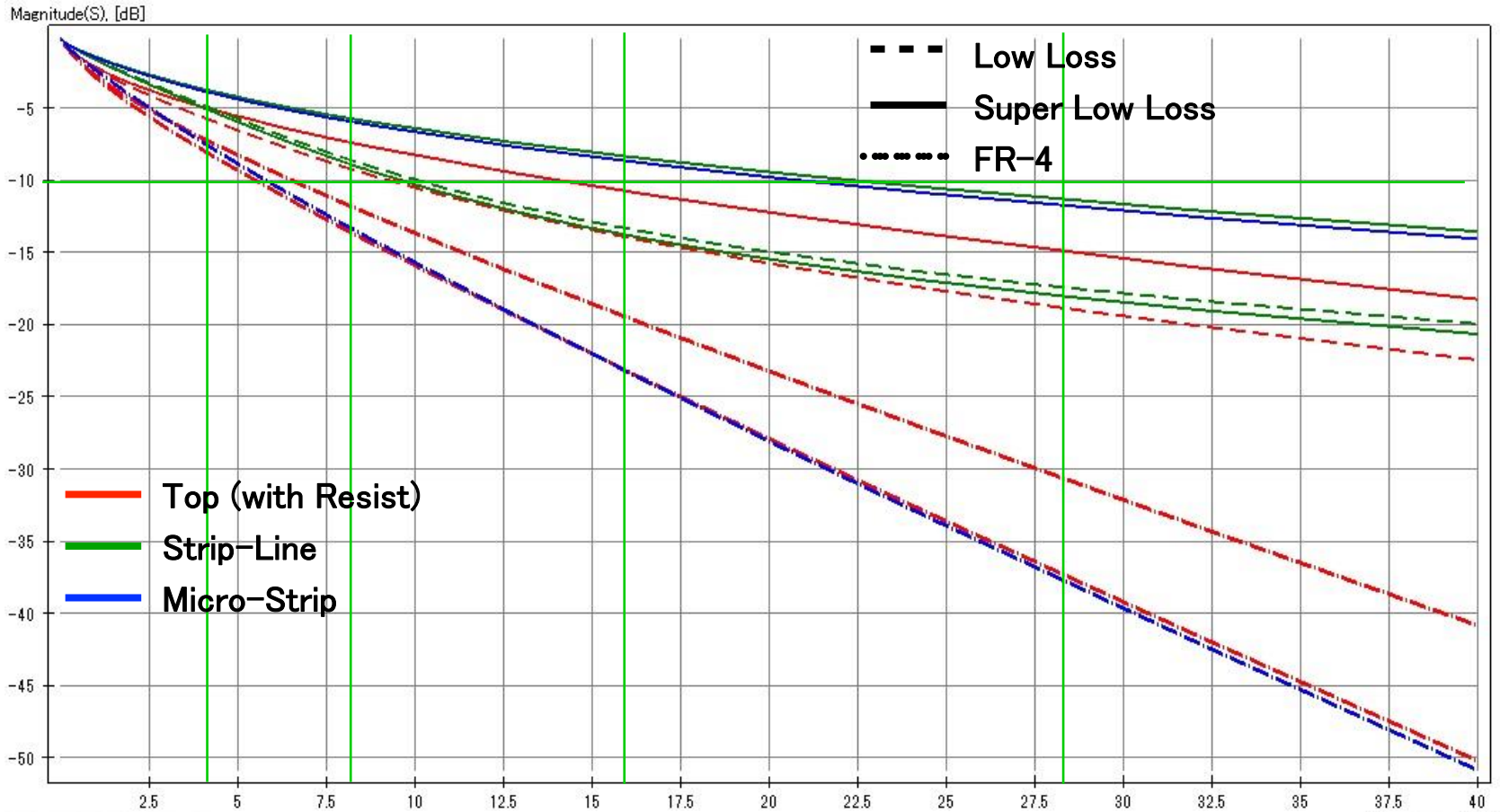
- Low Loss Material, Micro-Strip-line
  - Line Width: 100 $\mu$ m (Single Line Impedance = 50 ohm)



# Differential Line

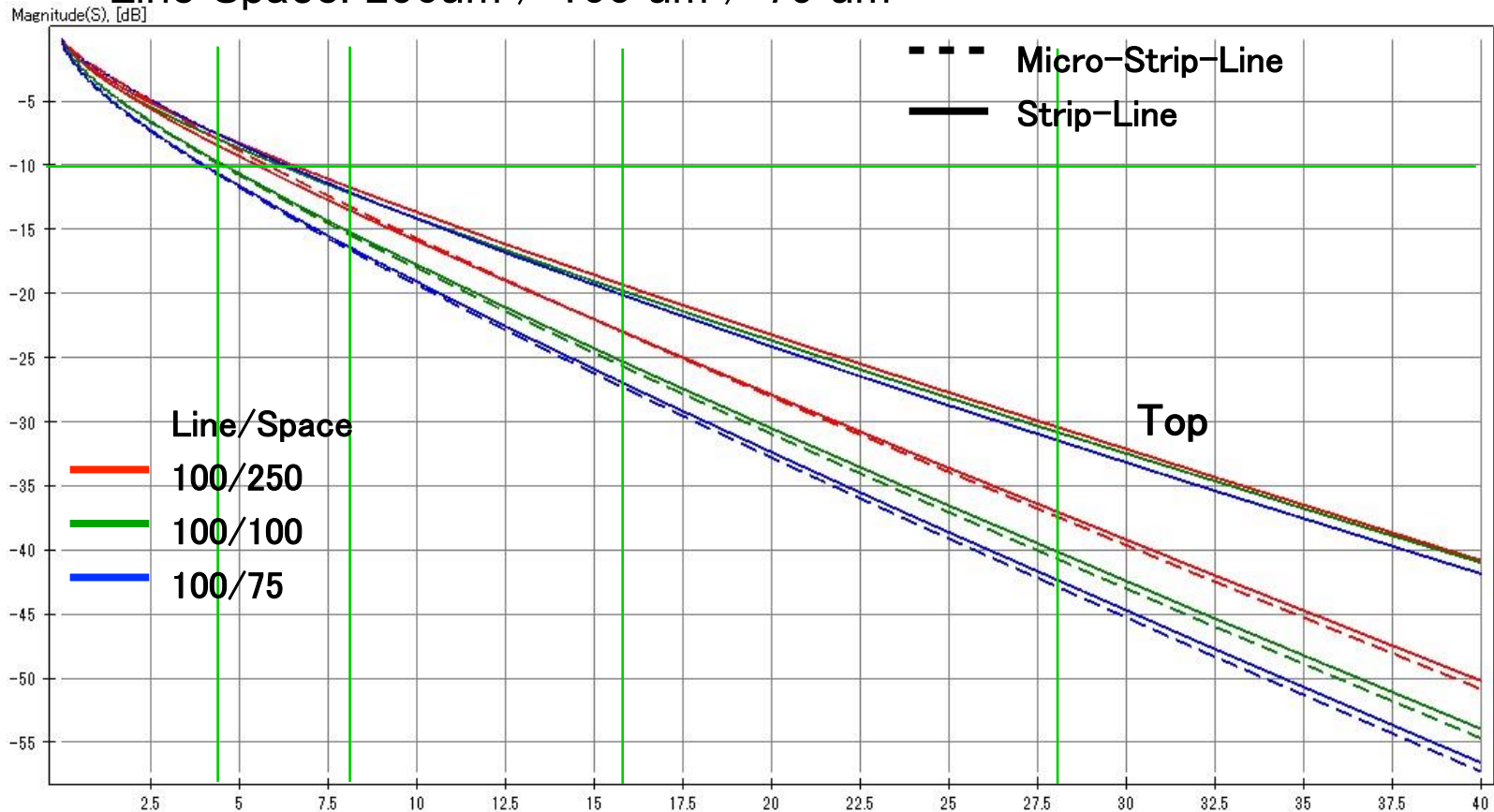
- Different Materials

- $L/S = 100 \text{ } \mu\text{m}/250 \text{ } \mu\text{m}$   $Z_{\text{diff}} \doteq 100 \text{ } \Omega$



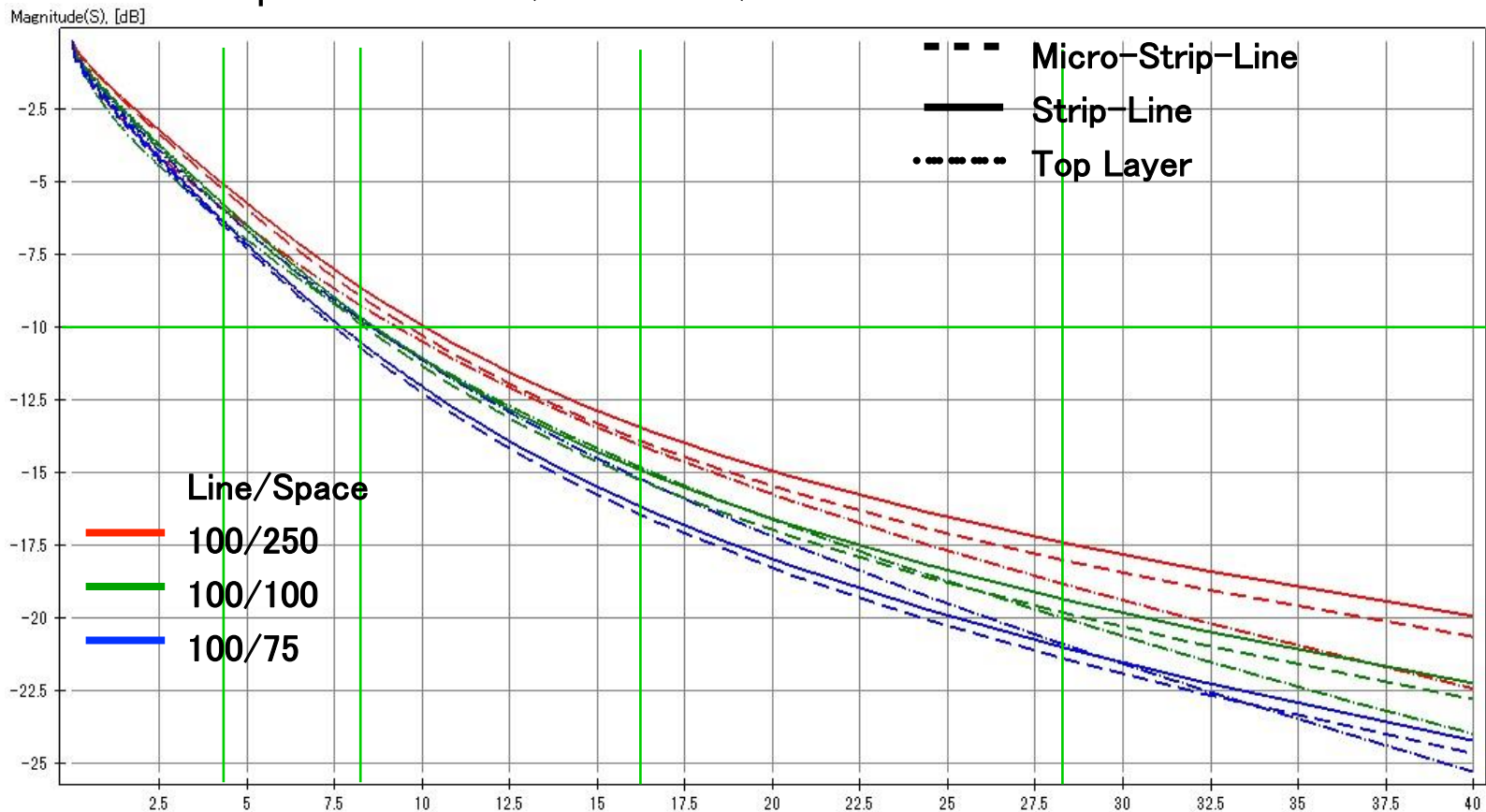
# Differential Line (FR-4)

- Different Space
  - Line Width 100  $\mu\text{m}$  (Single 50 ohm)
  - Line Space: 250 $\mu\text{m}$  / 100  $\mu\text{m}$  / 75  $\mu\text{m}$



# Differential Line (Low-Loss)

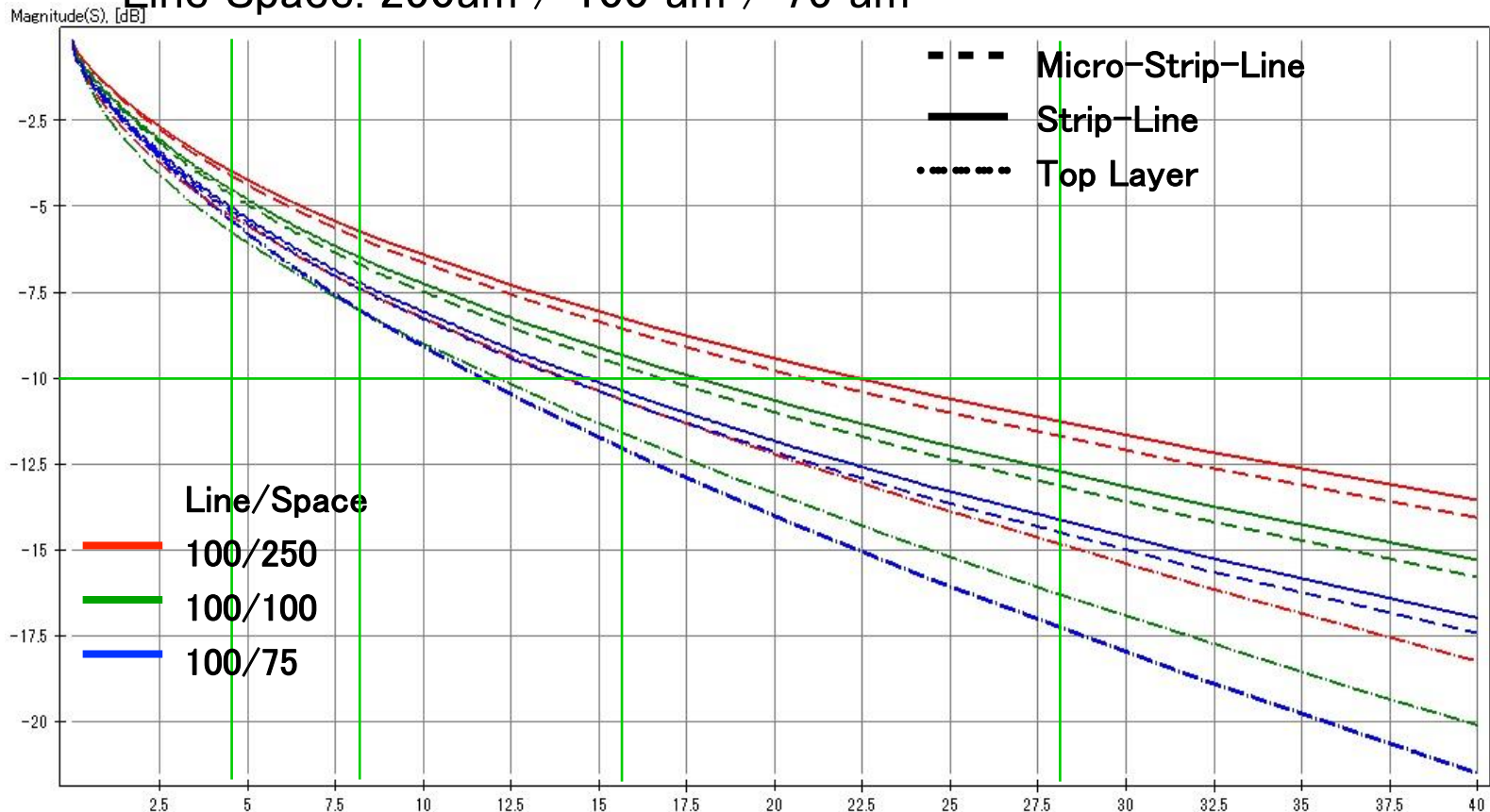
- Different Space
  - Line Width 100  $\mu\text{m}$  (Single 50 ohm)
  - Line Space: 250 $\mu\text{m}$  / 100  $\mu\text{m}$  / 75  $\mu\text{m}$





# Differential Line (Super-Low-Loss)

- Different Space
  - Line Width 100  $\mu\text{m}$  (Single 50 ohm)
  - Line Space: 250 $\mu\text{m}$  / 100  $\mu\text{m}$  / 75  $\mu\text{m}$



# Conclusion

- Line Width vs. Loss
  - Narrow Etch has advantage for Dielectric Loss
    - Less efficient Dipole
  - Wide Etch has advantage for Resistance Loss
    - Larger effective cross-section area
- Thick Copper has advantage for Resistance Loss
- Wide Differential Space is stable but low etch density
- Resist-Ink has effect for surface etch

